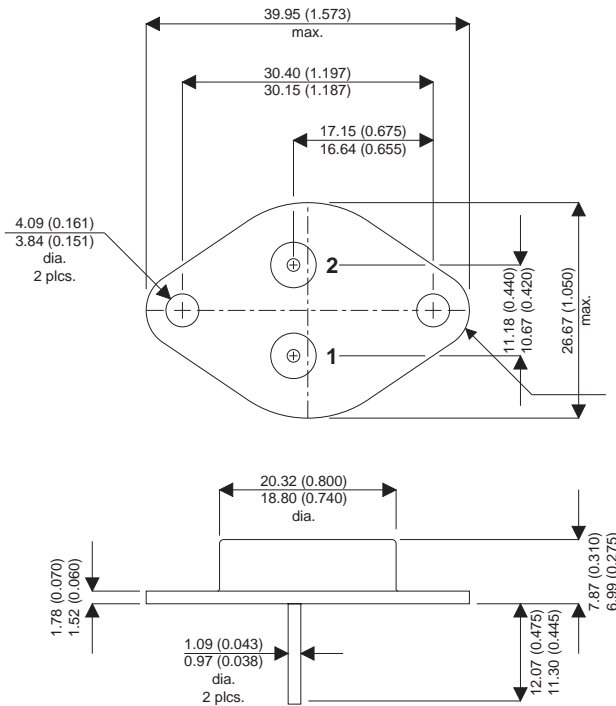


MECHANICAL DATA

Dimensions in mm (inches)



TO-3 Metal Package

Pin 1 – Gate Pin 2 – Source Case – Drain

**N-CHANNEL
POWER MOSFET**

V_{DSS} **100V**
 $I_{D(cont)}$ **28A**
 $R_{DS(on)}$ **0.077Ω**

FEATURES

- HERMETICALLY SEALED TO-3 METAL PACKAGE
- SIMPLE DRIVE REQUIREMENTS
- SCREENING OPTIONS AVAILABLE

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{GS}	Gate – Source Voltage	$\pm 20V$
I_D	Continuous Drain Current ($V_{GS} = 0, T_{case} = 25^{\circ}C$)	28A
I_D	Continuous Drain Current ($V_{GS} = 0, T_{case} = 100^{\circ}C$)	20A
I_{DM}	Pulsed Drain Current ¹	112A
P_D	Power Dissipation @ $T_{case} = 25^{\circ}C$	125W
	Linear Derating Factor	1W/ $^{\circ}C$
E_{AS}	Single Pulse Avalanche Energy ²	250mJ
I_{AR}	Avalanche Current ²	28A
E_{AR}	Repetitive Avalanche Energy ²	12.5mJ
dv/dt	Peak Diode Recovery ³	5.5V/ns
T_J, T_{stg}	Operating and Storage Temperature Range	-55 to +150 $^{\circ}C$
T_L	Lead Temperature 1.6mm (0.63") from case for 10 sec.	300 $^{\circ}C$

Notes

- 1) Pulse Test: Pulse Width $\leq 300\mu s, \delta \leq 2\%$
- 2) @ $V_{DD} = 25V, L \geq 480\mu H, R_G = 25\Omega, Peak I_L = 28A, Starting T_J = 25^{\circ}C$
- 3) @ $I_{SD} \leq 28A, di/dt \leq 170A/\mu s, V_{DD} \leq BV_{DSS}, T_J \leq 150^{\circ}C, Suggested R_G = 9.1\Omega$

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
STATIC ELECTRICAL RATINGS					
BV_{DSS}	Drain – Source Breakdown Voltage	$V_{GS} = 0$ $I_D = 1mA$	100		V
$\Delta BV_{DSS} / \Delta T_J$	Temperature Coefficient of Breakdown Voltage	Reference to $25^{\circ}C$ $I_D = 1mA$		0.13	$V/^{\circ}C$
$R_{DS(on)}$	Static Drain – Source On-State Resistance ¹	$V_{GS} = 10V$ $I_D = 20A$		0.077	Ω
		$V_{GS} = 10V$ $I_D = 28A$		0.089	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250mA$	2	4	V
g_{fs}	Forward Transconductance ¹	$V_{DS} \geq 15V$ $I_{DS} = 20A$	9.1		S (\bar{O})
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0$ $V_{DS} = 0.8BV_{DSS}$ $T_J = 125^{\circ}C$		25	μA
				250	
I_{GSS}	Forward Gate – Source Leakage	$V_{GS} = 20V$		100	nA
I_{GSS}	Reverse Gate – Source Leakage	$V_{GS} = -20V$		-100	
DYNAMIC CHARACTERISTICS					
C_{iss}	Input Capacitance	$V_{GS} = 0$		1660	pF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		550	
C_{riss}	Reverse Transfer Capacitance	$f = 1MHz$		120	
Q_g	Total Gate Charge	$V_{GS} = 10V$	30	59	nC
Q_{gs}	Gate – Source Charge	$I_D = 28A$	2.4	12	
Q_{gd}	Gate – Drain (“Miller”) Charge	$V_{DS} = 0.5BV_{DSS}$	12	30.7	
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50V$ $I_D = 28A$ $R_G = 9.1\Omega$		21	ns
t_r	Rise Time			145	
$t_{d(off)}$	Turn-Off Delay Time			21	
t_f	Fall Time			105	
SOURCE – DRAIN DIODE CHARACTERISTICS					
I_S	Continuous Source Current			28	A
I_{SM}	Pulse Source Current ²			112	
V_{SD}	Diode Forward Voltage ¹	$I_S = 28A$ $T_J = 25^{\circ}C$ $V_{GS} = 0$		1.5	V
t_{rr}	Reverse Recovery Time	$I_F = 28A$ $T_J = 25^{\circ}C$		400	ns
Q_{rr}	Reverse Recovery Charge ¹	$d_i / d_t \leq 100A/\mu s$ $V_{DD} \leq 50V$		2.9	μC
t_{on}	Forward Turn-On Time		Negligible		
PACKAGE CHARACTERISTICS					
L_D	Internal Drain Inductance (measured from 6mm down drain lead to centre of die)		5.0		nH
L_S	Internal Source Inductance (from 6mm down source lead to source bond pad)		13		
THERMAL CHARACTERISTICS					
$R_{\theta JC}$	Thermal Resistance Junction – Case			1.67	$^{\circ}C/W$
$R_{\theta CS}$	Thermal Resistance Case – Sink		0.12		
$R_{\theta JA}$	Thermal Resistance Junction – Ambient			30	

Notes

- 1) Pulse Test: Pulse Width $\leq 300ms$, $\delta \leq 2\%$
- 2) Repetitive Rating – Pulse width limited by maximum junction temperature.

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